GI127 **PNP EPITAXIAL PLANAR TRANSISTOR**

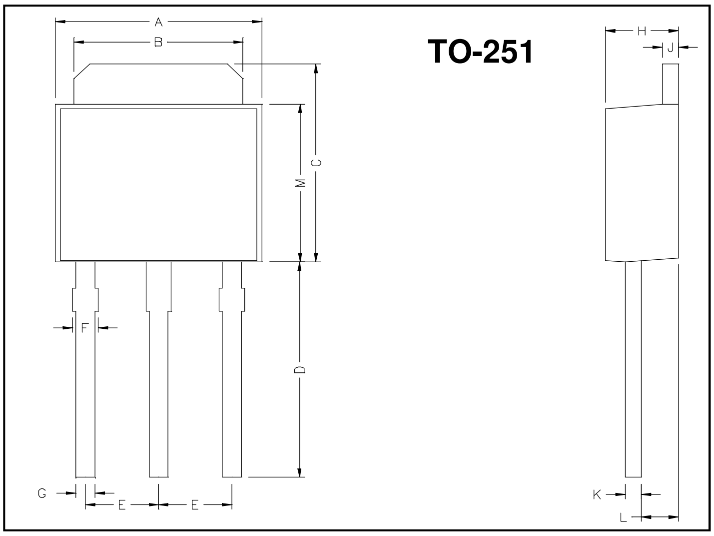
Description

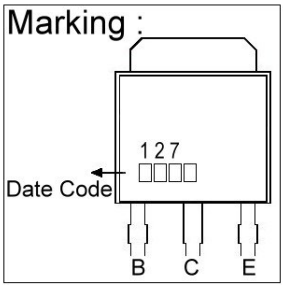
The GI127 is designed for use in general purposes and low speed switching applications.

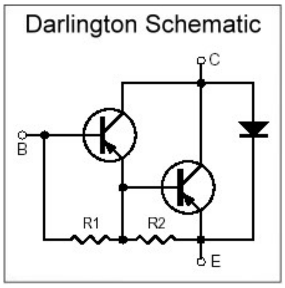
Features

- High DC current gain
- Built-in a damper diode at E-C

Package Dimensions







REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	7.20	7.80	K	0.45	0.60
E	2.30 REF.		L	0.90	1.50
F	0.60	0.90	M	5.40	5.80

Absolute Maximum Ratings at Ta = 25℃

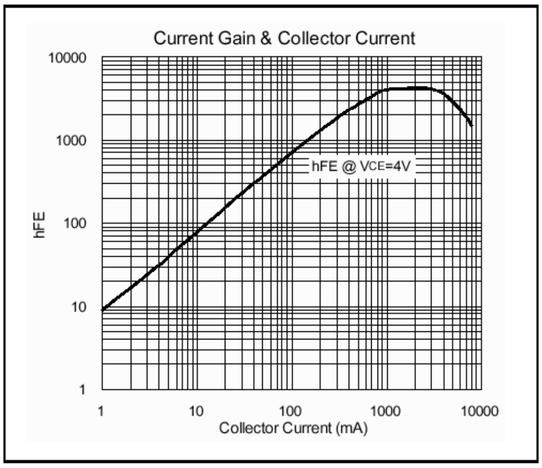
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	BVCBO	-100	V
Collector to Emitter Voltage	BVCEO	-100	V
Emitter to Base Voltage	BVEBO	-5	V
Collector Current	IC	-5	A
Total Power Dissipation(Tc=25℃)	PD	20	W

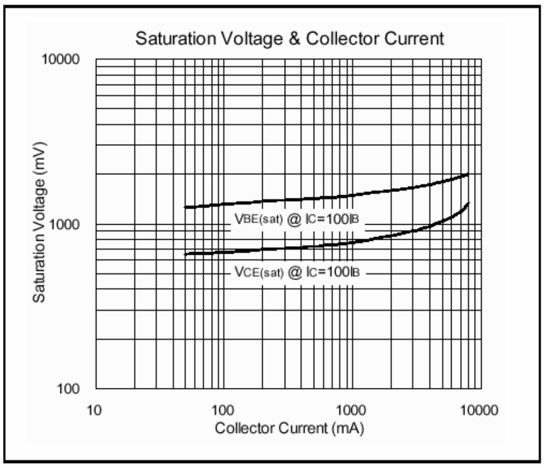
Electrical Characteristics **(Rating at 25℃ ambient temperature unless otherwise specified)**

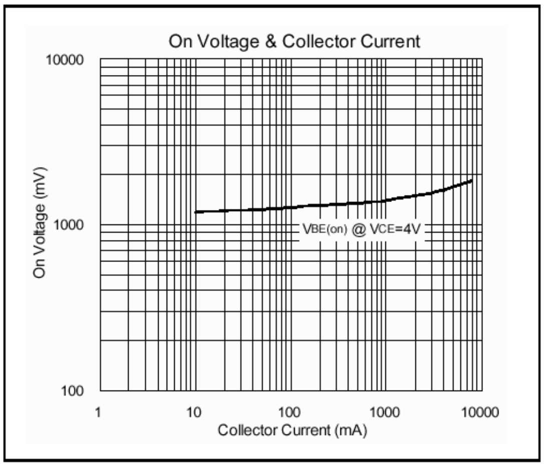
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-100	-	-	V	I_C=-1mA, I_E=0
BV_{CEO}	-100	-	-	V	I_C=-30mA, I_B=0
BV_{EBO}	-5	-	-	V	I_E=-1mA, I_C=0
I_{CBO}	-	-	-10	μA	V_{CB}=-100V, I_E=0
I_{CEX}	-	-	-10	μA	V_{CE}=-100V, $V_{BE(off)}$=-1.5V
I_{EBO}	-	-	-2	mA	V_{EB}=-5V, I_C=0
*$V_{CE(sat)}$1	-	-	-2	V	I_C=-3A, I_B=-12mA
*$V_{CE(sat)}$2	-	-	-4	V	I_C=-5A, I_B=-20mA
*$V_{BE(sat)}$	-	-	-4	V	I_C=-5A, I_B=-50mA
*$V_{BE(on)}$	-	-	-2.8	V	V_{CE}=-3V, I_C=-3A
*h_{FE}1	1	-	-	K	V_{CE}=-3V, I_C=-500mA
*h_{FE}2	1	-	-	K	V_{CE}=-3V, I_C=-3A
Cob	-	-	300	pF	V_{CB}=-10V, f=0.1MHz

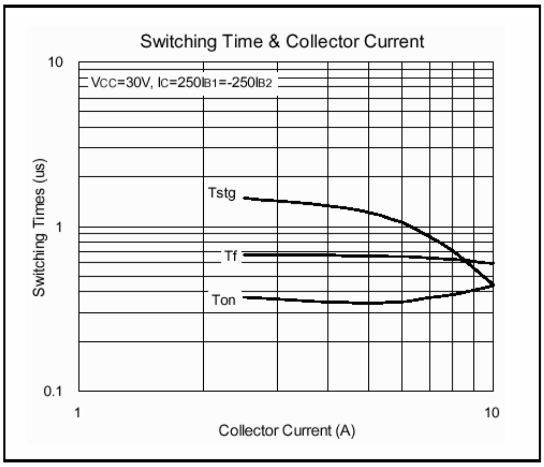
* Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%

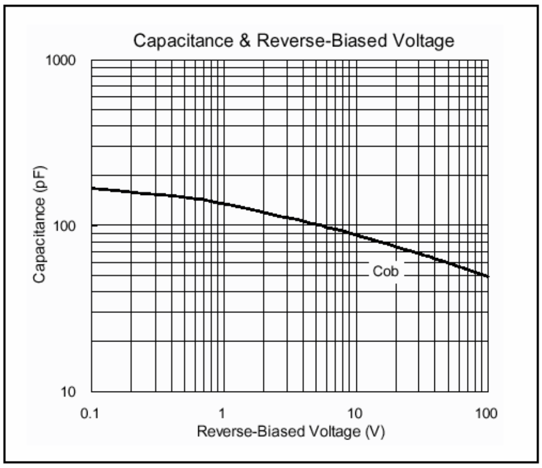
Characteristics Curve

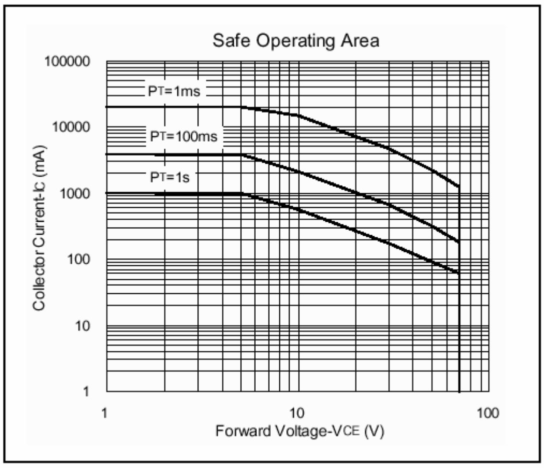












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